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## Description

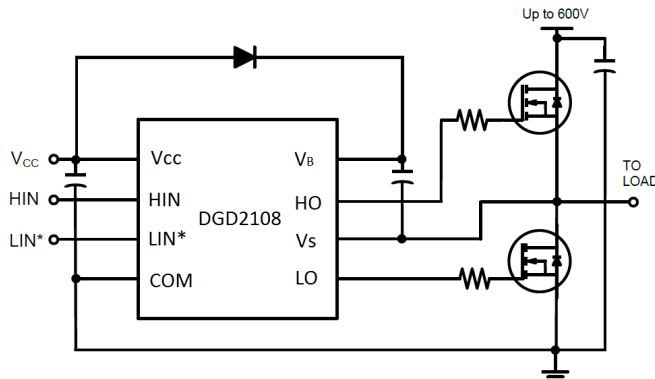
The DGD2108 is a high-voltage / high-speed gate driver capable of driving N-Channel MOSFETs and IGBTs in a half bridge configuration. High-voltage processing techniques enable the DGD2108's high-side to switch to 600V in a bootstrap operation.

The DGD2108 logic inputs are compatible with standard TTL and CMOS levels (down to 3.3V) for easy interfacing with controlling devices. The driver outputs feature high-pulse current buffers designed for minimum driver cross conduction. Internal deadtime protects high-voltage MOSFETs.

The DGD2108 is offered in SO-8 package, the operating temperature extends from -40°C to +125°C.

## Applications

- DC-DC Converters
- DC-AC Inverters
- AC-DC Power Supplies
- Motor Controls
- Class D Power Amplifiers



Typical Configuration

## Features

- Floating High-Side Driver in Bootstrap Operation to 600V
- Drives Two N-Channel MOSFETs or IGBTs in a Half Bridge Configuration
- Outputs Tolerant to Negative Transients
- Internal Logic and Dead Time of 540ns to Protect MOSFETs
- Wide Logic and Low-Side Gate Driver Supply Voltage: 10V to 20V
- Logic Inputs (HIN and LIN\*) 3.3V Capability
- Schmitt Triggered Logic Inputs with Internal Pull Down
- Undervoltage Lockout for High and Low Side Drivers
- Extended Temperature Range: -40°C to +125°C
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony free. "Green" Device (Note 3)**

## Mechanical Data

- Case: SO-8 (Type TH)
- Case Material: Molded Plastic. "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 3 per J-STD-020
- Terminals: Finish – Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 <sup>Ⓔ</sup>
- Weight: 0.075 grams (Approximate)



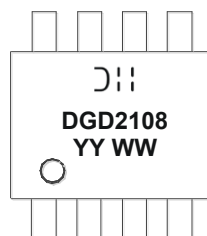
SO-8  
Top View

## Ordering Information (Note 4)

Product	Marking	Reel Size (inches)	Tape Width (mm)	Quantity Per Reel
DGD2108S8-13	DGD2108	13	12	2,500

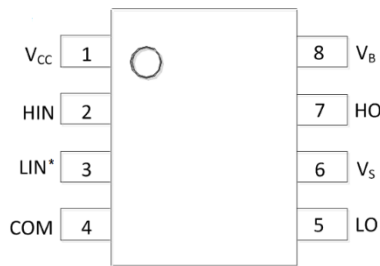
- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
  2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

## Marking Information



DII = Manufacturer's Marking  
 DGD2108 = Product Type Marking Code  
 YY = Year (ex: 19 = 2019)  
 WW = Week (01 to 53)

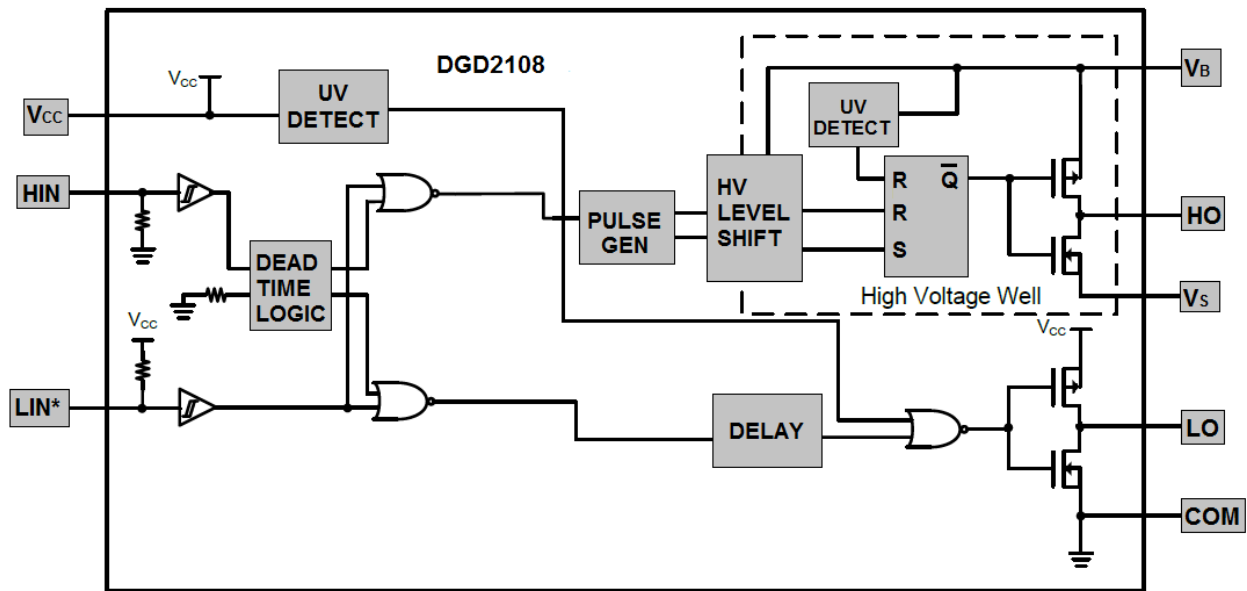
Pin Diagrams



Pin Descriptions

Pin Number	Pin Name	Function
1	V <sub>CC</sub>	Low-side and logic fixed supply
2	HIN	Logic input for high-side gate driver output, in phase with HO
3	LIN*	Logic input for low-side gate driver output, out of phase with LO
4	COM	Low-side return
5	LO	Low-side gate drive output
6	V <sub>S</sub>	High-side floating supply return
7	HO	High-side gate drive output
8	V <sub>B</sub>	High-side floating supply

Functional Block Diagram



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**Absolute Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
High-Side Floating Supply Voltage	V <sub>B</sub>	-0.3 to +624	V
High-Side Floating Supply Offset Voltage	V <sub>S</sub>	V <sub>B</sub> -24 to V <sub>B</sub> +0.3	V
High-Side Floating Output Voltage	V <sub>HO</sub>	V <sub>S</sub> -0.3 to V <sub>B</sub> +0.3	V
Offset Supply Voltage Transient	dV <sub>S</sub> / dt	50	V/ns
Low-Side and Logic Fixed Supply Voltage	V <sub>CC</sub>	-0.3 to +24	V
Low-Side Output Voltage	V <sub>LO</sub>	-0.3 to V <sub>CC</sub> +0.3	V
Logic Input Voltage (HIN and LIN*)	V <sub>IN</sub>	-0.3 to V <sub>CC</sub> +0.3	V

**Thermal Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation Linear Derating Factor (Note 5)	P <sub>D</sub>	0.625	W
Thermal Resistance, Junction to Ambient (Note 5)	R <sub>θJA</sub>	200	°C/W
Operating Temperature	T <sub>J</sub>	+150	°C
Lead Temperature (Soldering, 10s)	T <sub>L</sub>	+300	
Storage Temperature Range	T <sub>STG</sub>	-55 to +150	

Note: 5. When mounted on a standard JEDEC 2-layer FR-4 board.

**Recommended Operating Conditions**

Parameter	Symbol	Min	Max	Unit
High-Side Floating Supply Absolute Voltage	V <sub>B</sub>	V <sub>S</sub> + 10	V <sub>S</sub> + 20	V
High-Side Floating Supply Offset Voltage	V <sub>S</sub>	(Note 6)	600	V
High-Side Floating Output Voltage	V <sub>HO</sub>	V <sub>S</sub>	V <sub>B</sub>	V
Low-Side and Logic Fixed Supply Voltage	V <sub>CC</sub>	10	20	V
Low-Side Output Voltage	V <sub>LO</sub>	0	V <sub>CC</sub>	V
Logic Input Voltage	V <sub>IN</sub>	0	5	V
Ambient Temperature	T <sub>A</sub>	-40	+125	°C

Note: 6. Logic operation for V<sub>S</sub> of -5V to +600V.

**DC Electrical Characteristics** ( $V_{BIAS}$  ( $V_{CC}$ ,  $V_{BS}$ ) = 15V, @ $T_A$  = +25°C, unless otherwise specified.) (Note 7)

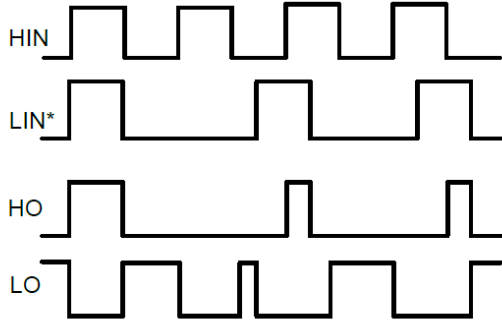
Parameter	Symbol	Min	Typ	Max	Unit	Conditions
Logic "1" Input Voltage (Note 8)	$V_{IH}$	2.5	—	—	V	$V_{CC} = 10V$ to 20V
Logic "0" Input Voltage (Note 8)	$V_{IL}$	—	—	0.6	V	$V_{CC} = 10V$ to 20V
High Level Output Voltage, $V_{BIAS} - V_O$	$V_{OH}$	—	0.05	0.2	V	$I_O = 2mA$
Low Level Output Voltage, $V_O$	$V_{OL}$	—	0.2	0.1	V	$I_O = 2mA$
Offset Supply Leakage Current	$I_{LK}$	—	—	50	$\mu A$	$V_B = V_S = 600V$
Quiescent $V_{BS}$ Supply Current	$I_{BSQ}$	20	75	130	$\mu A$	$V_{IN} = 0V$ or 5V
Quiescent $V_{CC}$ Supply Current	$I_{CCQ}$	0.4	1.0	1.6	mA	$V_{IN} = 0V$ or 5V
Logic "1" Input Bias Current	$I_{IN+}$	—	5	20	$\mu A$	$HIN = 5V$ , $LIN^* = 0V$
Logic "0" Input Bias Current	$I_{IN-}$	—	—	5	$\mu A$	$HIN = 0V$ , $LIN^* = 5V$
$V_{BS}$ Supply Undervoltage Positive Going Threshold	$V_{BSUV+}$	8.0	8.9	9.8	V	—
$V_{BS}$ Supply Undervoltage Negative Going Threshold	$V_{BSUV-}$	7.4	8.2	9.0	V	—
$V_{CC}$ Supply Undervoltage Positive Going Threshold	$V_{CCUV+}$	8.0	8.9	9.8	V	—
$V_{CC}$ Supply Undervoltage Negative Going Threshold	$V_{CCUV-}$	7.4	8.2	9.0	V	—
Hysteresis	$V_{CCUVH}$	0.3	0.7	—	V	—
	$V_{BSUVH}$					
Output High Short Circuit Pulsed Current	$I_{O+}$	120	290	—	mA	$V_O = 0V$ , $PW \leq 10\mu s$
Output Low Short Circuit Pulsed Current	$I_{O-}$	250	600	—	mA	$V_O = 15V$ , $PW \leq 10\mu s$

- Notes:
- The  $V_{IN}$  and  $I_{IN}$  parameters are referenced to  $V_{SS}$  and are applicable to the two logic input pins: HIN and LIN\*. The  $V_O$  and  $I_O$  parameters are referenced to COM and are applicable to the respective output pins: HO and LO.
  - For optimal operation, it is recommended that the input pulses (HIN and LIN\*) should have a minimum amplitude of 2.5V with a minimum pulse width of 1 $\mu s$ .

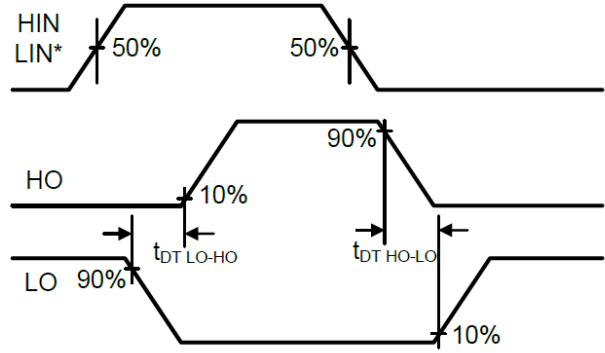
**AC Electrical Characteristics** ( $V_{BIAS}$  ( $V_{CC}$ ,  $V_{BS}$ ) = 15V,  $C_L = 1000pF$ , @ $T_A$  = +25°C, unless otherwise specified.)

Parameter	Symbol	Min	Typ	Max	Unit	Conditions
Turn-On Propagation Delay	$t_{ON}$	—	220	300	ns	$V_S = 0V$
Turn-Off Propagation Delay	$t_{OFF}$	—	200	280	ns	$V_S = 0V$ or 600V
Delay Matching, $ t_{ON} - t_{OFF} $	$t_{DMON}$	—	—	30	ns	—
Turn-On Rise Time	$t_r$	—	100	220	ns	$V_S = 0V$
Turn-Off Fall Time	$t_f$	—	35	80	ns	$V_S = 0V$
Deadtime: $t_{DT LO-HO}$ & $t_{DT HO-LO}$	$t_{DT}$	400	540	680	ns	—
Deadtime Matching: $t_{DT LO-HO} - t_{DT HO-LO}$	$t_{MDT}$	—	0	60	ns	—

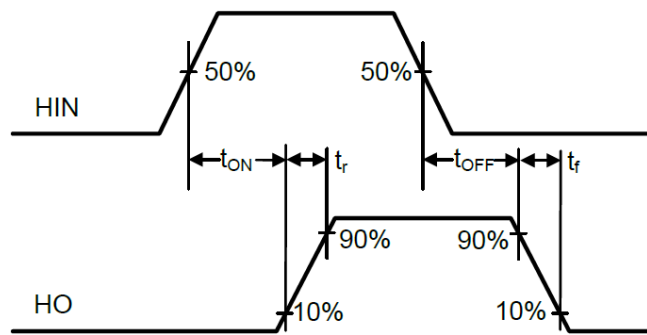
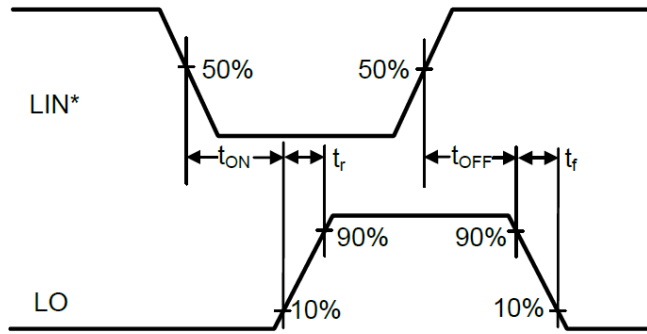
**Timing Waveforms**



**Figure 1.** Input / Output Timing Diagram



**Figure 2.** Deadtime Waveform Definitions



**Figure 3.** Switching Time Waveform Definitions

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**Typical Performance Characteristics** ( $V_{CC} = 15V$ ,  $@T_A = +25^{\circ}C$ , unless otherwise specified.)

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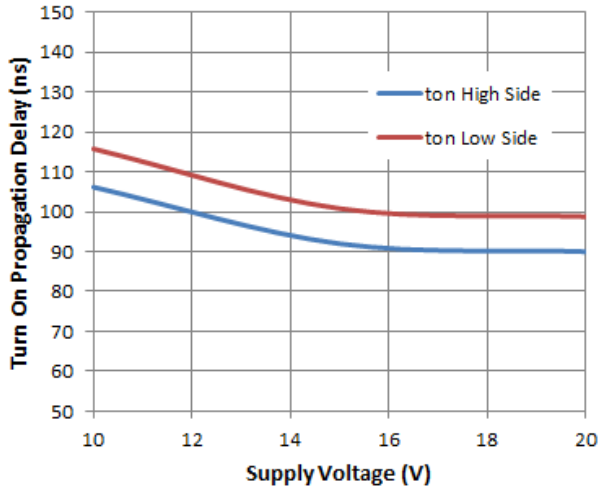


Figure 4. Turn-on Propagation Delay vs. Supply Voltage

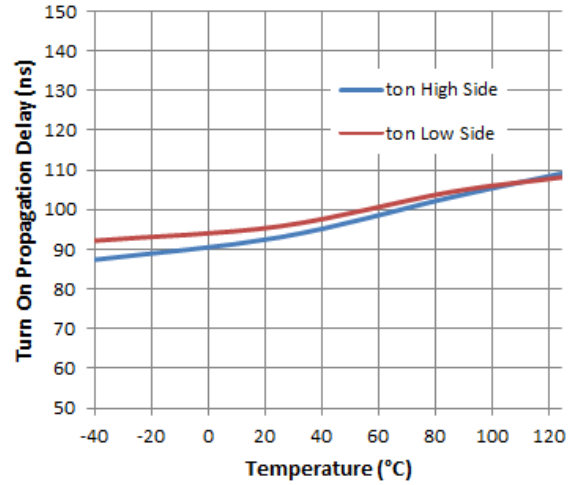


Figure 5. Turn-on Propagation Delay vs. Temperature

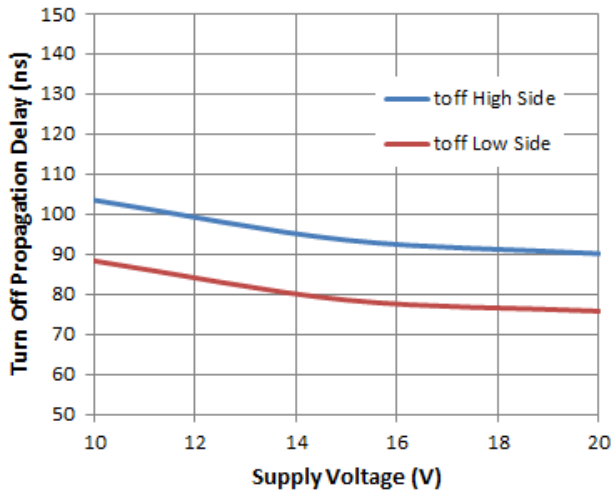


Figure 6. Turn-off Propagation Delay vs. Supply Voltage

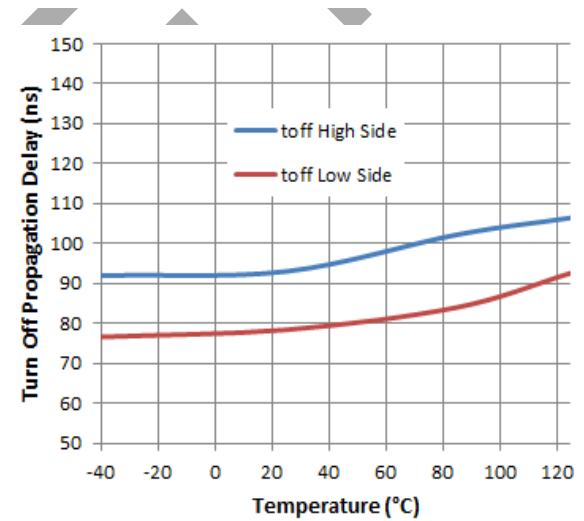


Figure 7. Turn-off Propagation Delay vs. Temperature

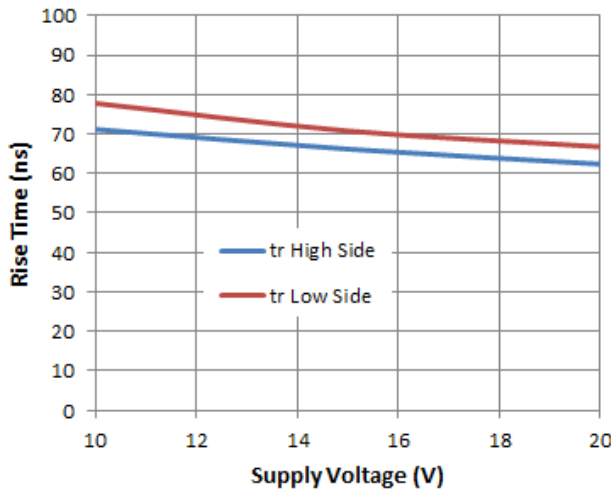


Figure 8. Rise Time vs. Supply Voltage

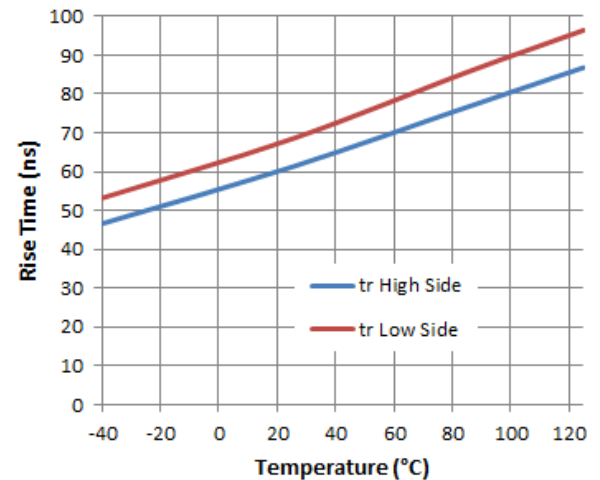


Figure 9. Rise Time vs. Temperature

Typical Performance Characteristics (continued)

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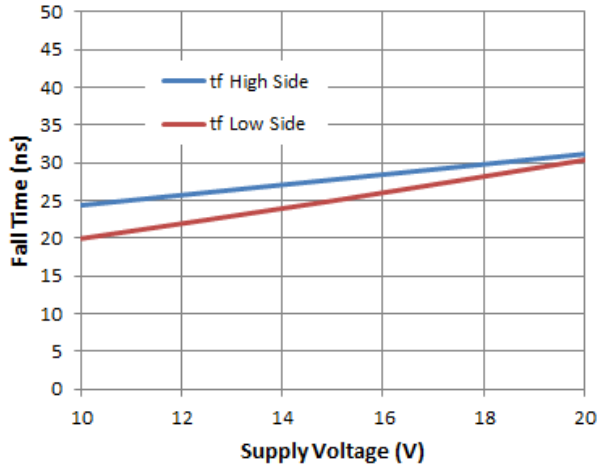


Figure 10. Fall Time vs. Supply Voltage

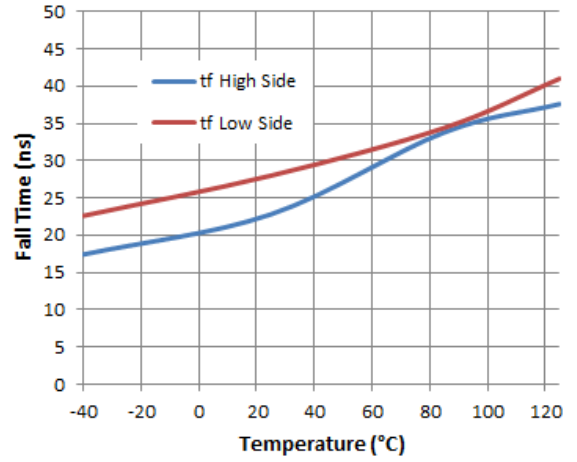


Figure 11. Fall Time vs. Temperature

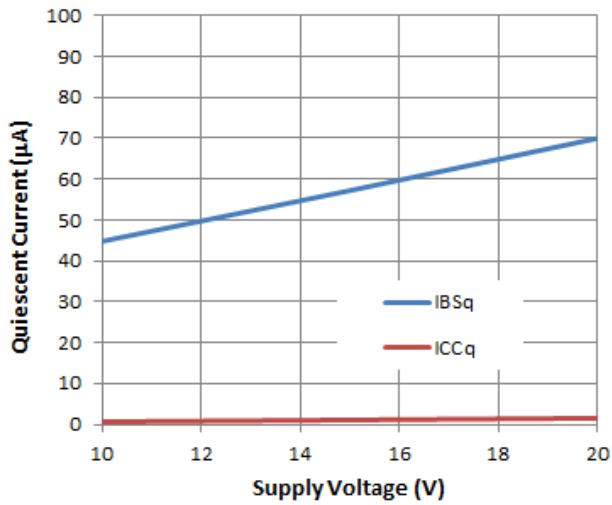


Figure 12. Quiescent Current vs. Supply Voltage

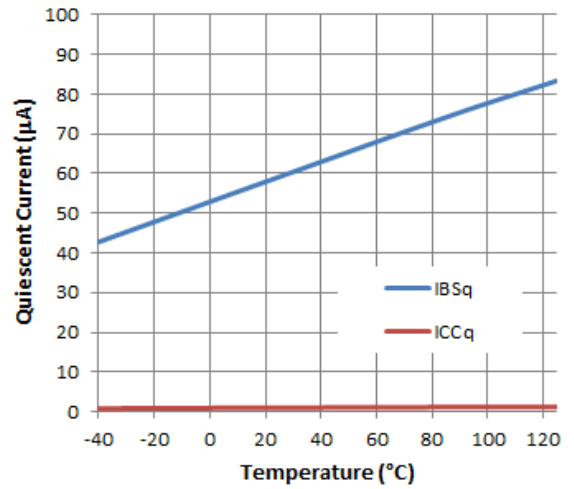


Figure 13. Quiescent Current vs. Temperature

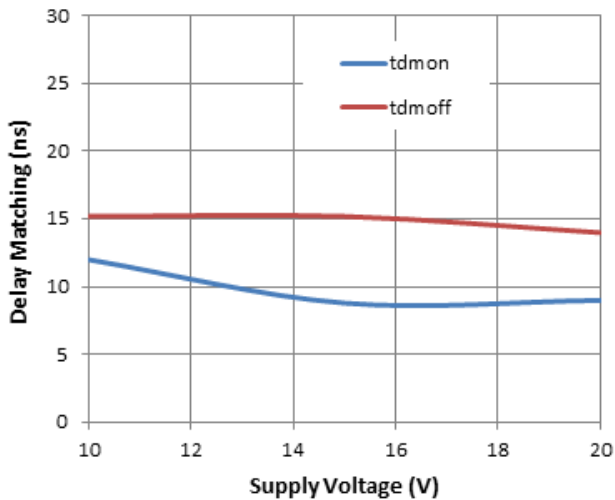


Figure 14. Delay Matching vs. Supply Voltage

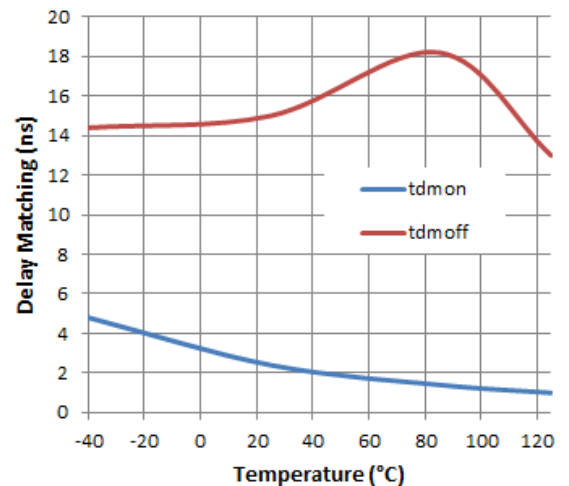
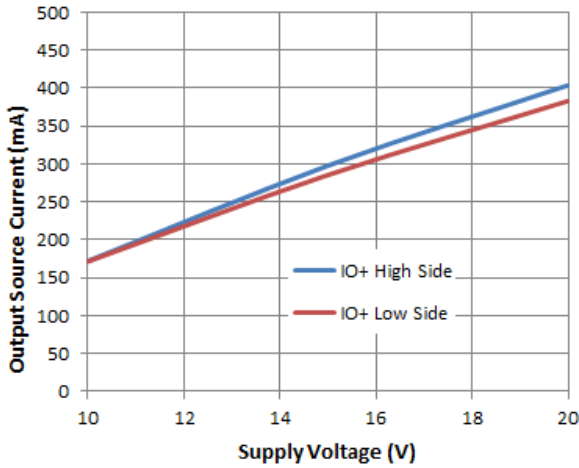


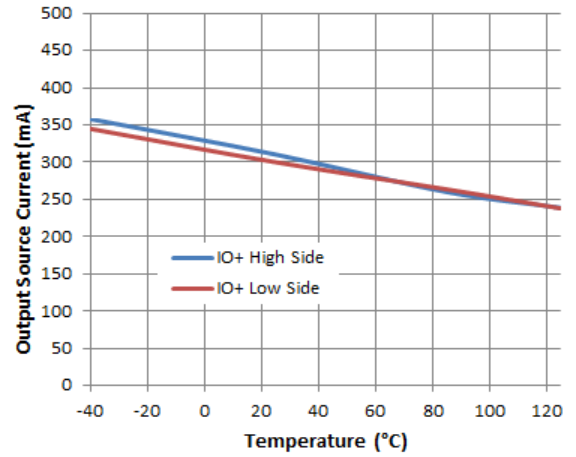
Figure 15. Delay Matching vs. Temperature

**Typical Performance Characteristics** (continued)

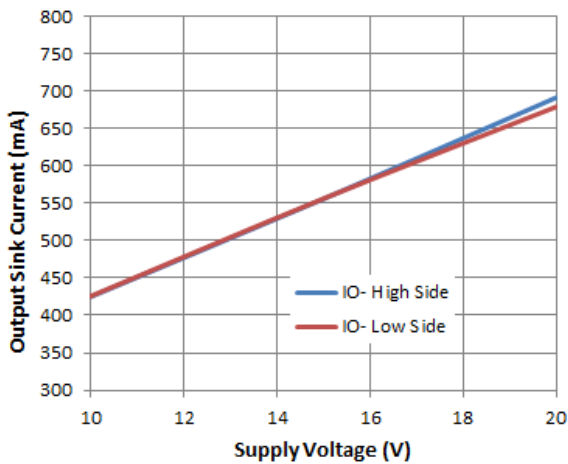
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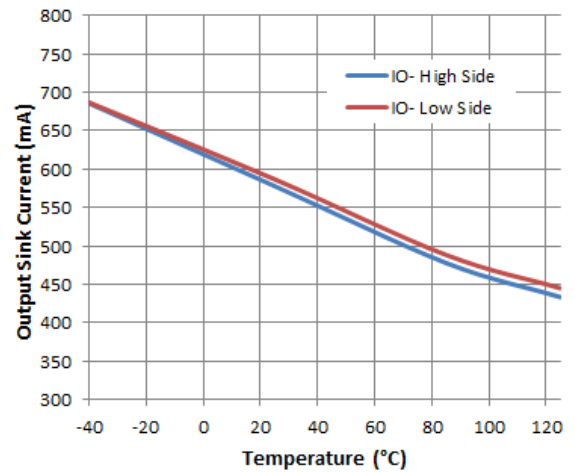
**Figure 16.** Output Source Current vs. Supply Voltage



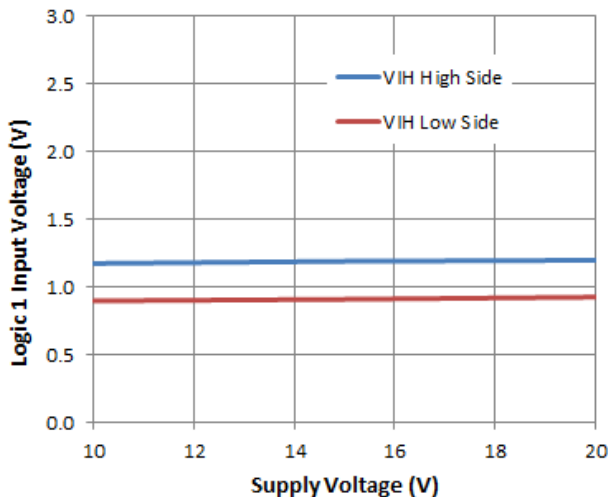
**Figure 17.** Output Source Current vs. Temperature



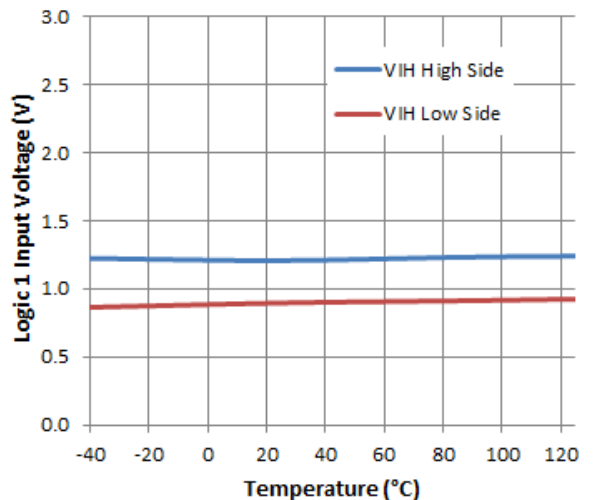
**Figure 18.** Output Sink Current vs. Supply Voltage



**Figure 19.** Output Sink Current vs. Temperature



**Figure 20.** Logic 1 Input Voltage vs. Supply Voltage



**Figure 21.** Logic 1 Input Voltage vs. Temperature



Typical Performance Characteristics (continued)

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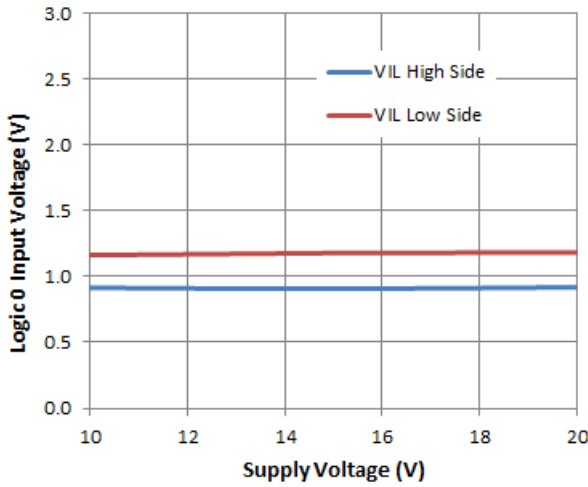


Figure 22. Logic 0 Input Voltage vs. Supply Voltage

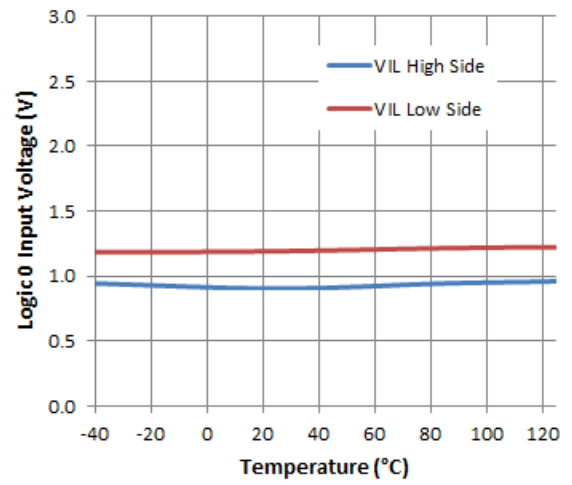


Figure 23. Logic 0 Input Voltage vs. Temperature

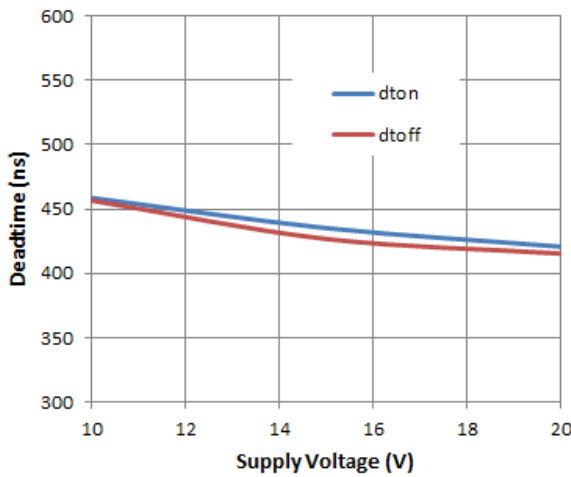


Figure 24. Deadtime vs. Supply Voltage

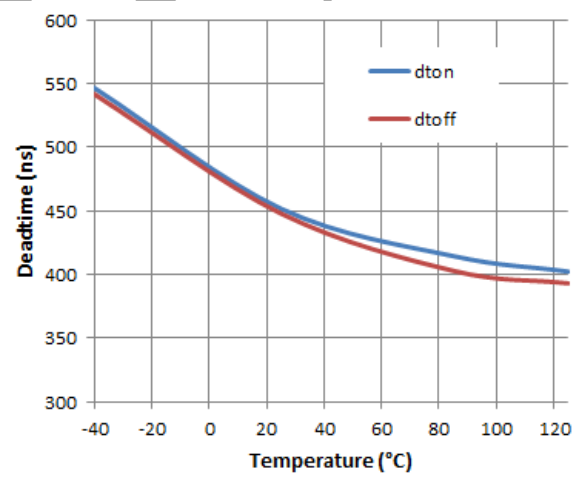


Figure 25. Deadtime vs. Temperature

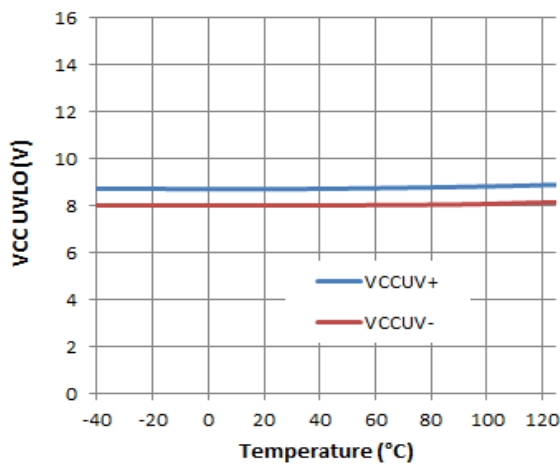


Figure 26. VCC UVLO vs. Temperature

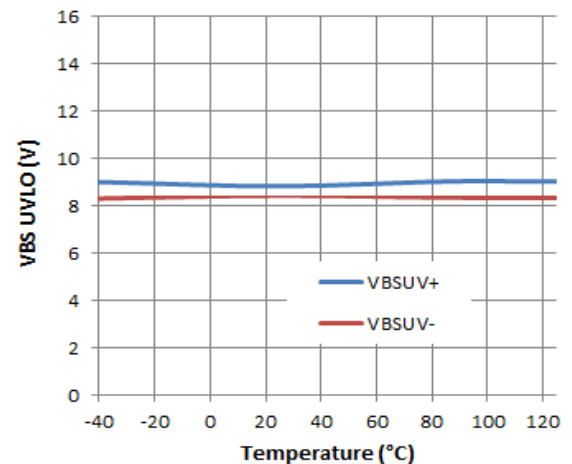


Figure 27. VBS UVLO vs. Temperature

**Typical Performance Characteristics** (continued)

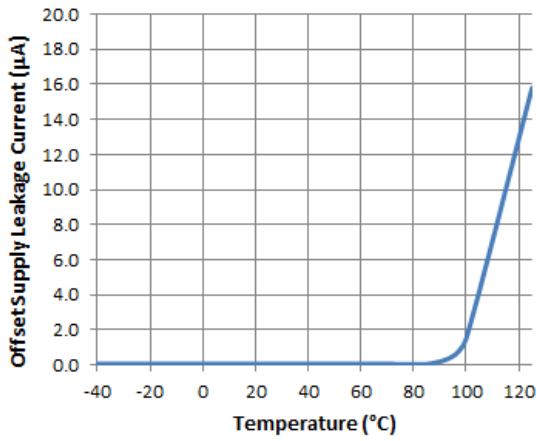


Figure 28. Offset Supply Leakage Current vs. Temperature

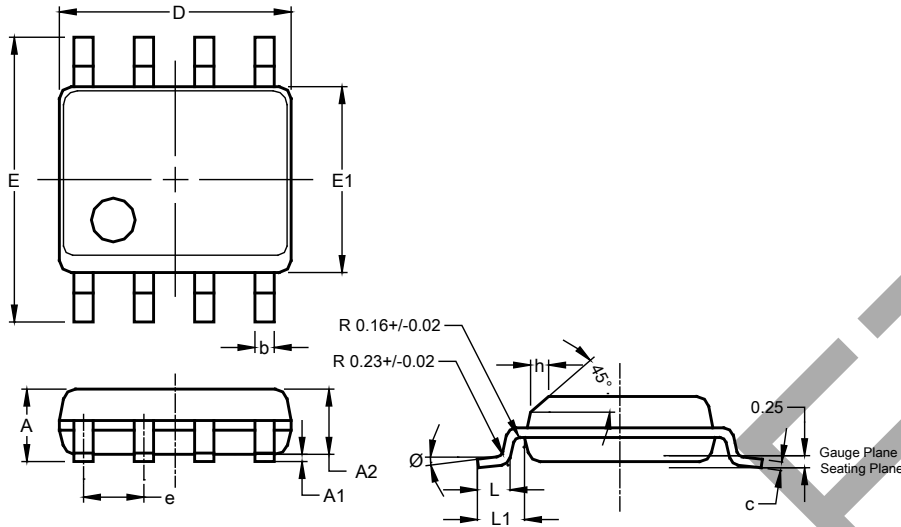
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**Package Outline Dimensions**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

**SO-8 (Type TH)**

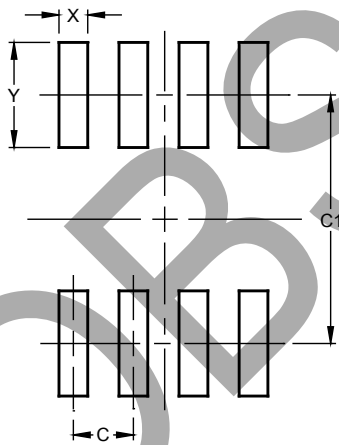


SO-8 (Type TH)			
Dim	Min	Max	Typ
A	1.35	1.75	--
A1	0.10	0.25	--
A2	--	--	1.45
b	0.35	0.51	--
c	0.190	0.248	--
D	4.80	5.00	4.90
E	5.80	6.20	6.00
E1	3.80	4.00	3.90
e	--	--	1.27
h	0.25	0.50	--
L	0.41	1.27	--
L1	--	--	1.04
Ø	0°	8°	--
All Dimensions in mm			

**Suggested Pad Layout**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

**SO-8 (Type TH)**



Dimensions	Value (in mm)
C	1.27
C1	5.20
X	0.60
Y	2.20

Note: For high voltage applications, the appropriate industry sector guidelines should be considered with regards to creepage and clearance distances between device Terminals and PCB tracking.

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